IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Original): An aqueous dispersion for chemical mechanical polishing comprising abrasive grains, wherein the abrasive grains include:

(A) simple particles composed of at least one selected from inorganic particvles and organic particles and

(B) composite particles.

Claim 2 (Original): The aqueous dispersion for chemical mechanical polishing according to claim 1, wherein the simple particles (A) making up the abrasive grains are composed of inorganic particles, and the composite particles (B) are composed of inorganic organic composite particles obtained by integrally combining organic particles with inorganic particles.

Claim 3 (Original): The aqueous dispersion for chemical mechanical polishing according to claim 1 or 2, wherein the overall content of all the abrasive grains is 0.11 to 20 % by mass, the content of the simple particles (A) is 0.1 to 19.99 % by mass, and the content of the composite particles (B) is 0.01 to 19.9 % by mass.

Claim 4 (Currently Amended): The aqueous dispersion for chemical mechanical polishing according to ~~any one of claims 1 to 3~~ claim 1, wherein a value of a specific removal rate ration (RMB/RCu) represented by a ratio of the removal rate (RBM) of a barrier metal film to the removal rate (RCu) of a copper film in the case where the copper film and barrier metal film are polished under the same conditions is 0.5 to 200.

Claim 5 (Currently Amended): The aqueous dispersion for chemical mechanical polishing according to ~~any one of claims 1 to 3~~ claim 1, wherein the value of the specific removal rate ration (RMB/RCu) represented by a ratio of the removal rate (RBM) of a barrier metal film to the removal rate (RCu) of a copper film in the case where the copper film and barrier metal film are polished under the same conditions is 10 to 200.

Claim 6 (Currently Amended): The aqueous dispersion for chemical mechanical polishing according to ~~any one of claims 1 to 3~~ claim 1, wherein the value of the specific removal rate ration (RMB/RCu) represented by a ratio of the removal rate (RBM) of a barrier metal film to the removal rate (RCu) of a copper film in the case where the copper film and barrier metal film are polished under the same conditions is 0.5 to 3.

Claim 7 (Currently Amended): A process for producing a semiconductor device, comprising the step of polishing a surface to be polished of a semiconductor material with the aqueous dispersion for chemical mechanical polishing according to ~~any one of claims 1 to 6~~ claim 1.

Claim 8 (Original): A process for producing a semiconductor device, comprising the first polishing treatment step of mainly polishing a copper film of a surface to be polished of a semiconductor material and the second polishing treatment step of mainly polishing a barrier metal film with the aqueous dispersion for chemical mechanical polishing according to claim 5 or 6, conducted after the first polishing treatment step.

DISCUSSION OF AMENDMENT

Claims 2-7 are currently amended.

The claims have been amended to remove improper multiple dependencies.

The claims are supported by the claims and specification, as originally filed.

Upon entry of the amendment, claims 1-8 will be active.

No new matter has been added by the amendments